

10039284
12/31/01

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10039284	12/31/2001	257			Geo. Pratt

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2811

**CONTINUING DATA VERIFIED:

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** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		GS 174
Verified and Acknowledged Examiners's initials		
TITLE : High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source		

U.S. DEPT. OF COMM (PAT. & TM.-PTC-436L (Rev. 12-94))

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Primary Examiner	
		Application Examiner	
PREPARED FOR ISSUE		WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

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